

This Page Is Inserted by IFW Operations  
and is not a part of the Official Record

## **BEST AVAILABLE IMAGES**

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

**IMAGES ARE BEST AVAILABLE COPY.**

**As rescanning documents *will not* correct images,  
please do not report the images to the  
Image Problem Mailbox.**

(19)



JAPANESE PATENT OFFICE

## PATENT ABSTRACTS OF JAPAN

(11) Publication number: 56126916 A

(43) Date of publication of application: 05 . 10 . 81

(51) Int. Cl.

H01L 21/22  
H01L 21/302

(21) Application number: 55030173

(22) Date of filing: 10 . 03 . 80

(71) Applicant: NIPPON TELEGR & TELEPH  
CORP <NTT>(72) Inventor: YOSHIKAWA AKIRA  
TAKEDA AKITSU  
OCHI OSAMU  
KUKI TOMOKO  
MIZUSHIMA YOSHIHIKO

(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

COPYRIGHT: (C)1981,JPO&amp;Japio

(57) Abstract:

**PURPOSE:** To diffuse Se easily and in high accuracy from a chalcogenide to which silver is added by a method wherein an amorphous chalcogenide layer, a principal ingredient thereof is Se, and a photoresist layer formed by stacking silver or a layer containing silver are made up on a substrate in a III-V group compound, and the surface is developed, coated with a heatproof film and thermally treated.

**CONSTITUTION:** A photoresist material 5 formed by laminating an amorphous chalcogenide 3 having 75 atom % Se and 25 atom % Ge and a layer 4 containing Ag is made up on a P type GaAs substrate 1, exposed 6 and developed. When a heatproof layer 8 of SiO<sub>2</sub>, Ti, etc. is built up on the chalcogenide 7 to which Ag is added and thermally treated, Se is diffused from the layer 7, and an N layer 9 is obtained. The heatproof layer 8 is removed, an insulating film 11 is opened, and an electrode 12 is attached. A mask is not required except the inorganic photoresist layer 5, the layer 7 can be formed in a pattern of high accuracy, and the layer 9 can be brought to necessary concentration by controlling heat treatment time.

